

Claim 11. (Amended) A method for fabricating a semiconductor device comprising the steps of:

b3 forming a gate electrode on a semiconductor layer;
forming impurity layers on both sides of said gate electrode in said semiconductor layer;
distributing a nonmetal element towards an inner portion of a substrate and in a region in the vicinity of a surface portion of said semiconductor layer;
depositing a metal film on said semiconductor layer; and
epitaxially growing a semiconductor-metal compound layer in the surface portion of said semiconductor layer by causing a reaction between an element included in said semiconductor layer and a metal included in said metal film through annealing carried out on said metal film.

b4 Claim 14. (Amended) The method for fabricating a semiconductor device of Claim 16, wherein said oxygen has a concentration of 4×10^{14} through $4 \times 10^{15} \text{ cm}^{-2}$.

[Please add the following new claims 15-16:]

b5 --15. (New) The method for fabricating a semiconductor device of claim 8, wherein the oxygen is distributed between a depth of 0.5nm and 5nm from the surface of the silicon layer.

16. (New) The method of fabricating a semiconductor device of claim 13, wherein the oxygen is distributed between a depth of 0.5nm and 5nm from the surface of the silicon layer.--

REMARKS

At the outset the Examiner is thanked for the review and consideration of the present application. The Examiner's Action dated August 5, 2002 has been received and its contents reviewed. Prior to this Amendment, claims 1-14 were pending in the instant application. By this amendment, claims 1, 9, 10, 11 and 14 have been amended, and claims 15 and 16 have been newly added. Accordingly, claims 1-16 are pending in the instant application, of which claims 1 and 11 are independent.

Referring now to the detailed Office Action, claims 9, 10, and 14 are rejected under 35 U.S.C. §112, second paragraph, as indefinite and failing to particularly point out and distinctly